

November 2013

FGH60N60SMD 600 V, 60 A Field Stop IGBT

Features

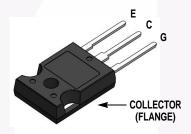
- Maximum Junction Temperature: T_J = 175°C
- Positive Temperaure Co-efficient for easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.9 V(Typ.) @ I_C = 60 A
- · High Input Impedance
- Fast Switching: E_{OFF} = 7.5 uJ/A
- · Tightened Parameter Distribution
- · RoHS Compliant

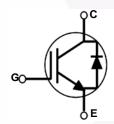
Applications

• Solar Inverter, UPS, Welder, PFC, Telecom, ESS

General Description

Using novel field stop IGBT technology, Fairchild's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		600	V
V _{GES}	Gate to Emitter Voltage		± 20	V
*GES	Transient Gate-to-Emitter Voltage		± 30	V
Ic	Collector Current	$@ T_C = 25^{\circ}C$	120	Α
10	Collector Current	$@ T_C = 100^{\circ}C$	60	Α
I _{CM (1)}	Pulsed Collector Current		180	Α
I _F	Diode Forward Current	$^{\circ}$ T _C = 25 $^{\circ}$ C	60	Α
'F	Diode Forward Current	$@ T_C = 100^{\circ}C$	30	Α
I _{FM (1)}	Pulsed Diode Maximum Forward Current		180	Α
P _D	Maximum Power Dissipation	$@ T_C = 25^{\circ}C$	600	W
י ט	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	300	W
T _J	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.25	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case	-	1.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH60N60SMD	FGH60N60SMD	TO-247	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \mu\text{A}$	-	0.6	-	V/oC
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μА
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 250 \mu A, V_{CE} = V_{GE}$	3.5	4.5	6.0	V
02()	-	I _C = 60 A, V _{GE} = 15 V	-	1.9	2.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 60 A, V _{GE} = 15 V, T _C = 175°C	-	2.1	-	V
Dynamic C	Characteristics					
C _{ies}	Input Capacitance		-	2915	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	270	-	pF
C _{res}	Reverse Transfer Capacitance	1 = 1 101112	-	85	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-/	18	27	ns
t _r	Rise Time	-	-	47	70	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 60 \text{ A},$	-	104	146	ns
t _f	Fall Time	$R_G = 3 \Omega$, $V_{GE} = 15 V$,	-	50	68	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C	-	1.26	1.94	mJ
E _{off}	Turn-Off Switching Loss		-	0.45	0.6	mJ
E _{ts}	Total Switching Loss		-	1.71	2.54	mJ
t _{d(on)}	Turn-On Delay Time		-	18	- \	ns
t _r	Rise Time		-	41	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 60 \text{ A},$	-	115	-	ns
t _f	Fall Time	$R_G = 3 \Omega$, $V_{GE} = 15 V$,	-	48	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 175°C	-	2.1	-	mJ
E _{off}	Turn-Off Switching Loss]	-	0.78	-	mJ
E _{ts}	Total Switching Loss]	-	2.88	-	mJ

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Q_g	Total Gate Charge		-	189	284	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 60 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	20	30	nC
Q _{gc}	Gate to Collector Charge	1 VGE - 10 V	=	91	137	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	ons	Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 30 A	$T_C = 25^{\circ}C$	-	2.1	2.7	V
FIVI	Diode i di waid vollage	.,	$T_{\rm C} = 175^{\rm o}{\rm C}$	-	1.7	-	
E _{rec}	Reverse Recovery Energy		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	79	-	uJ
t _{rr}	Diode Reverse Recovery Time	I _F =30 A, di _F /dt = 200 A/μs	$T_C = 25^{\circ}C$	-	30	39	ns
111	2.000 1.010.00 1.00010.) 1	i _F = 50 A, diβ/dt = 200 A/μs	$T_{\rm C} = 175^{\rm o}{\rm C}$	-	72	-	
Q _{rr}	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$	-	44	62	nC
~ II	2.000 reterois recovery emange		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	238	1	

Figure 1. Typical Output Characteristics

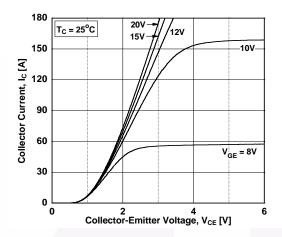


Figure 3. Typical Saturation Voltage Characteristics

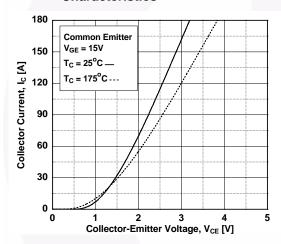


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

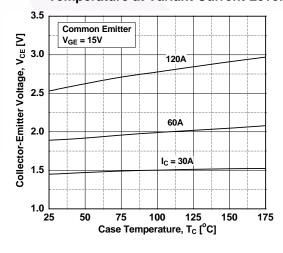


Figure 2. Typical Output Characteristics

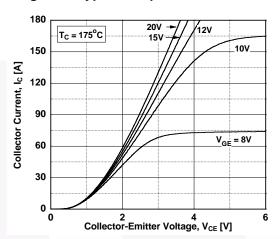


Figure 4. Transfer Characteristics

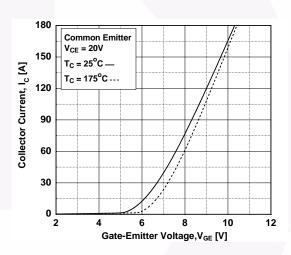


Figure 6. Saturation Voltage vs. V_{GE}

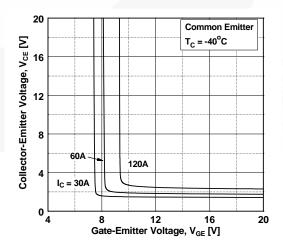


Figure 7. Saturation Voltage vs. V_{GE}

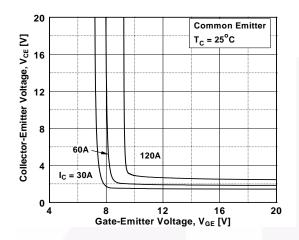


Figure 9. Capacitance Characteristics

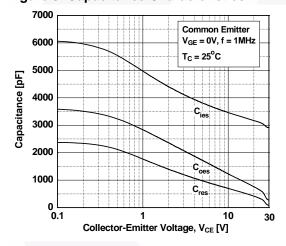


Figure 11. SOA Characteristics

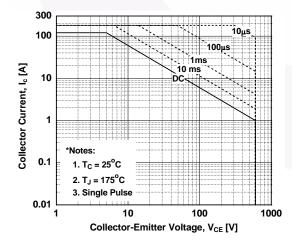


Figure 8. Saturation Voltage vs. V_{GE}

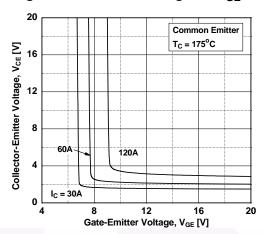


Figure 10. Gate charge Characteristics

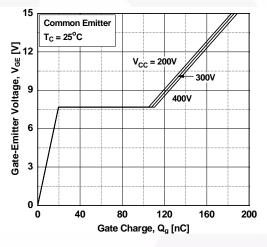


Figure 12. Turn-on Characteristics vs.
Gate Resistance

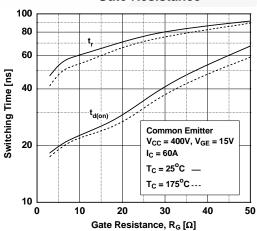


Figure 13. Turn-off Characteristics vs.
Gate Resistance

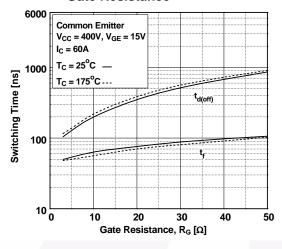


Figure 14. Turn-on Characteristics vs.
Collector Current

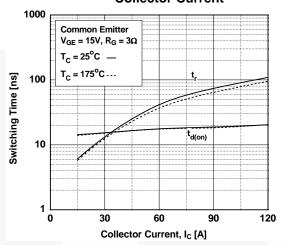


Figure 15. Turn-off Characteristics vs. Collector Current

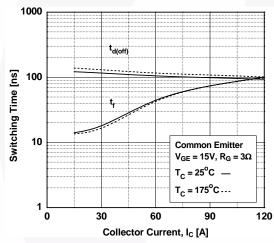


Figure 16. Switching Loss vs.

Gate Resistance

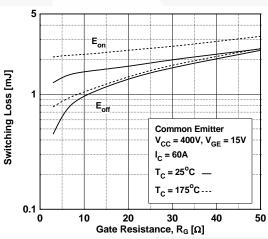


Figure 17. Switching Loss vs. Collector Current

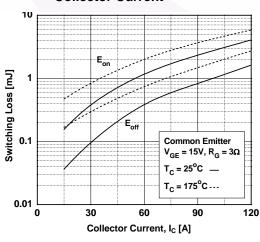


Figure 18. Turn off Switching SOA Characteristics

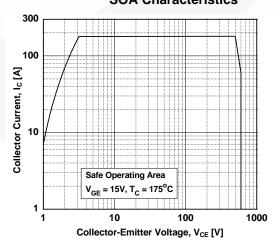


Figure 19. Current Derating

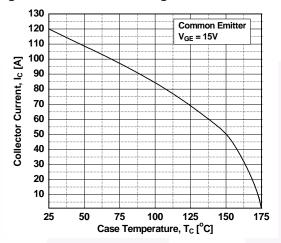


Figure 20. Load Current Vs. Frequency

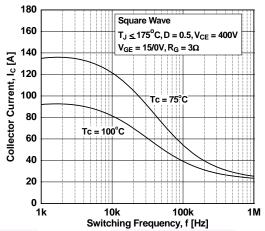


Figure 21. Forward Characteristics

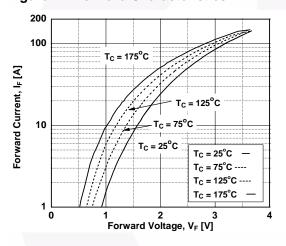


Figure 22. Reverse Current

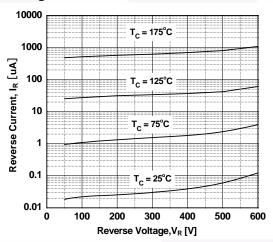


Figure 23. Stored Charge

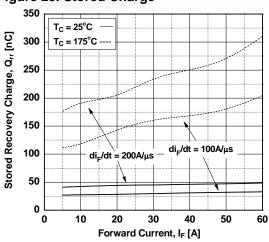


Figure 24. Reverse Recovery Time

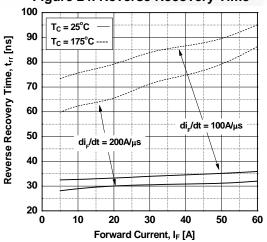


Figure 25.Transient Thermal Impedance of IGBT

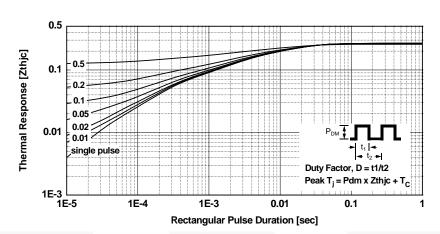
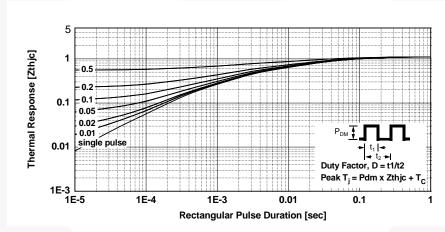


Figure 26. Transient Thermal Impedance of Diode



Mechanical Dimensions В 15.87 E φ^{3.65}/_{3.51}/_E Φ 0.254 Μ Β ΑΜ 12.81 E $\phi_{3.51}^{3.65}$ 5.58 E 1.35 Ø 5.20 F 13.08 MIN 3 16.25 E (1.60) 3 2.66 5.56 1.17 0.254 M B AM 11.12 NOTES: UNLESS OTHERWISE SPECIFIED. A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004. B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS. ALL DIMENSIONS ARE IN MILLIMETERS. D. DRAWING CONFORMS TO ASME Y14.5 - 1994 DOES NOT COMPLY JEDEC STANDARD VALUE

Figure 27. TO-247 3L - TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB

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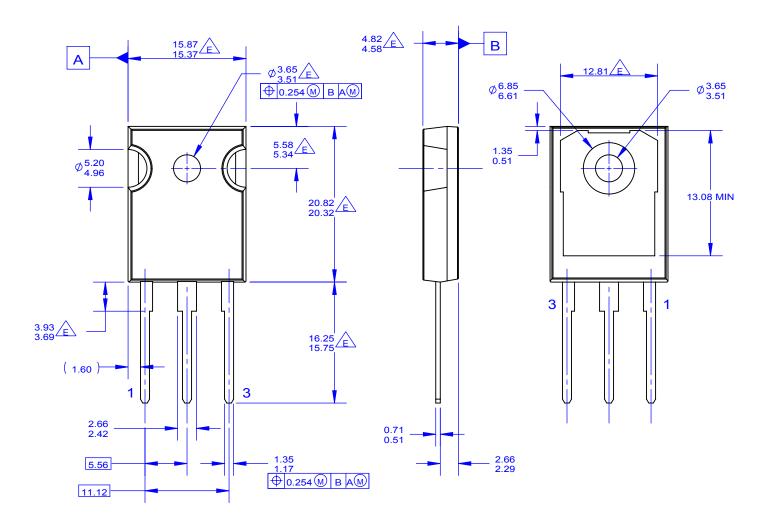
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